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**TRANSMITTAL
FORM**

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Total Number of Pages in This Submission

| | |
|--|-------------------------|
| Application Number | 09/699,466 |
| Filing Date | October 31, 2000 |
| First Named Inventor | Shunpei YAMAZAKI et al. |
| Group Art Unit | 2829 |
| Examiner Name | A. Sarkar |
| Total Number of Pages in This Submission | Attorney Docket Number |
| | 0756-2222 |

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ENCLOSURES (check all that apply)

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 Extension of Time Request
 Express Abandonment Request
 Information Disclosure Statement
 Certified Copy of Priority Document(s)
 Response to Missing Parts/ Incomplete Application
 Response to Missing Parts under 37 CFR 1.52 or 1.53

Assignment Papers (for an Application)
 Drawing(s)
 Declaration and Power of Attorney
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 Petition
 Petition to Convert to a Provisional Application
 Power of Attorney, Revocation Change of Correspondence Address
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 Request for Refund
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 Status Letter
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1. Change of Correspondence Address Form
2.
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Remarks

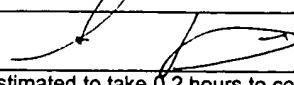
The Commissioner is hereby authorized to charge any additional fees required or credit any overpayments to Deposit Account No. for the above identified docket number.

SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT

| | |
|-------------------------|---|
| Firm or Individual name | Eric J. Robinson Robinson Intellectual Property Law Office, P.C. PMB 955 21010 Southbank Street Potomac Falls, VA 20165 |
| Signature |  |
| Date | May 20, 2002 |

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| Signature |  | Date | May 20, 2002 |

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

Shunpei YAMAZAKI et al

Serial No. 09/699,466

Filed: October 31, 2000

For: MEHTOD FOR FABRICATING A)

A SEMICONDUCTOR DEVICE)

Art Unit: 2829

Examiner: A. Sarkar



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AMENDMENT

Honorable Commissioner of Patents

Washington, D.C. 20231

Sir:

In response to the Office Action dated February 19, 2002 please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1, 4, 7, 11, 15, 20 and 26-28 as follows:

1. (Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film on an insulating surface; and

forming a semiconductor island having a tapered shape by patterning said semiconductor film, said tapered shape having an angle within a range of 20° to 50° between a side thereof and an underlying surface,

wherein irradiation of laser light is performed after forming said semiconductor film.

4. (Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film on an insulating surface;

✓
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✓
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